

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Hwang, et al.

Serial No.: 10/092,456

Confirmation No.: 1212

Filed:

(2)

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March 6, 2002

For: ETCHING METHODS FOR A

MAGNETIC MEMORY CELL STACK

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Examiner:

Group Art Unit: 2818

Dung Anh Le

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

CERTIFICATE OF MAILING

37 CFR 1.8

I hereby certify that this correspondence is being deposited on December 12, 2003 with the United States Postal Service as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450 Alexandria, VA 22313-1450.

Signature

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

The Applicants, and the Attorney who signs below on the basis of the information supplied by the inventor and the information in his file, submit herewith patents, publications, or other information of which they are aware, which may be material to the examination of this application and in respect of which there may be a duty to disclose in accordance with 37 CFR § 1.56.

While the information submitted in this Supplemental Information Disclosure Statement may be material pursuant to 37 CFR § 1.56, it is not intended to constitute an admission that any patent, publication, or other information referred to therein is prior art for this invention unless specifically designated as such.

In accordance with 37 CFR § 1.97, this Supplemental Information Disclosure Statement is not to be construed as a representation that a search has been made or that no other possibly material information as defined under 37 CFR § 1.56(a) exists.

The patents and/or publications submitted herewith are set forth on the attached Form PTO-1449.

Applicants certify that all references submitted with this disclosure were cited in a communication from a foreign patent office dated October 23, 2003, which communication is enclosed, not more than three months prior to the filing of this Supplemental Information Disclosure Statement.

If the sum of \$180.00 is due under 37 CFR § 1.17(p) pursuant to § 1.97, the Commissioner is hereby authorized to charge this fee, and any other fee necessary to make this submission timely, to the Deposit Account No.: 20-0782/AMAT/6437/LYC.

Respectfully submitted,

Lie-Yea Cheng

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Agent for Applicant(s)

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U.S. Department of Commerce, Patent and Trademark Office					Docket No.		Serial No.	
(PTO Form 1449 modified)					AMAT/6437/ETCH/METAL/JB1		10/092,456	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT					Applicant Hwang, et al.		Confirmation No. 1212	
(Use several sheets if necessary)					Filing Date		Group	
U.S. Patent Documents					March 6, 2002		2818	
U.S. Patent Documents								
*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date I Appropriate	
-	A1							
	A2							
	A3							
	A4						-	
	A5							•
Foreign Patent Documents								
*Examiner		Document	Date	Country	Class	Subclass	Translation	
Initial		Number					YES	NO
	B1							
	B2							
	В3							
	B4							
	B5							
OTHER ART								
*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.						
	C1	Jung, K.B., et al., "Long term stability of dry etched magnetoresistive random access memory elements", <i>Journal of Vacuum Science and Technology:Part A</i> ; American Institute of Physics, New York, U.S., Vol. 18, No. 1, January 2000 (2000-01), pp. 268-272, XP001145970, ISSN: 0734-2101.						
	C2	van Delft, F.C.M.J.M., et al., "The etch mechanisms of magnetic materials in an HCl plasma", Fusion Technology and Plasmas Session of the Twelth International Vacuum Congress (IVC-12) and Eighth International Conference on Solid Surfaces (ICSS-8), The Hague, Netherlands, 12-16 Oct. 1992, Vol. 200, No. 3, pp. 366-370, XP008022404, <i>Journal of Nuclear Materials</i> , May 1993, Netherlands, ISSN: 0022-3115.						
	C3	Cho, H. et al., "Inductively coupled plasma etching of CoFeB, CoZr, CoSm and FeMn thin films in interhalogen mixtures", <i>Materials Science and Engineering B (Solid-State Materials for Advanced Technology)</i> , 15 June 1999, Elsevier, Switzerland, Vol. B60, No. 2, pp. 107-111, XP004175032, ISSN: 0921-5107.						
Examiner					Date Considered			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.								